

AMENDMENTS TO THE CLAIMS:

This listing of claims replaces all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) A component comprising: having a hermetic seal, [[-]]
~~having a sandwich-like glued structure, the outside edges of which are aligned, comprising~~
[[-]] a chip (Ch) on the surface of which having a first chip face and a second chip
face, the first chip face comprising component structures (BS) and connector metallizations
associated with the component structures; connected with them are implemented,
[[-]] a frame structure (RS), which surrounds on the first chip face and adjacent to
the component structures; structure, and
[[-]] a diffusion-proof cover over the frame structure, the cover having a first cover
face and a second cover face, the first cover face being closer to the chip than the second
cover face; (AD),
[[-]] having a back face metallization that is on the second chip face, on sides of the
frame structure, and on sides of the cover; (RM) that reaches beyond the back face of the
chip, beyond all the butt edges (SK) of the sandwich-like structure,
[[-]] having underside contacts a contact on the second cover face; and (UK) on the
underside of the cover (AD) facing away from the chip,

[[~~-~~]] ~~having interfacial connections (DK) a connection~~ through the cover, which ~~connect the connection electrically connecting the component structures (BS) on the chip~~ with ~~and the contact; underside contacts~~ [[~~,~~]] ~~in electrically conductive manner,~~

[[~~-~~]] wherein the connection is ~~inside surfaces of the interfacial connections are~~ metallized ~~with an underside metallization (UM) and thereby sealed in diffusion proof~~ manner.

2. (Currently Amended) The component as recited in of claim 1, ~~in which a closed cavity is formed within the frame structure (RS), between wherein the chip (Ch) and the cover define a cavity that contains the component structures, within the sandwich-like structure.~~

3. (Currently Amended) The component as recited in of claim 1 or 2, in which wherein the frame structure comprises one or more interior structures that define one or more enclosures within the frame structure, the one or more enclosures exposing (RS) forms a runner (AL) that points towards the inside, or an insulated island (Rs_i), which surround another cavity within the sandwich-like structure, in which the connector metallizations (AM) on the surface of the chip (CH) lie exposed.

4. (Currently Amended) The component as recited in of claim 1 one of claims 1-3, further comprising wiring adjacent to the first cover face, the wiring being connected to the in which another wiring level (VE) is provided within the sandwich-like structure,

~~which is connected both with the connector metallizations (AM) and with to the~~
~~connection underside contacts (UK), by way of interfacial connections (DK).~~

5. (Currently Amended) The component as recited in of claim 1 one of claims 1 to
[[4]], in which further comprising, between the cover and the frame structure:

at least one ~~additional~~ intermediate layer; and

~~at least one wiring adjacent to the first cover face level (VE) are provided between~~
~~cover (AD) and frame structure (RS).~~

6. (Currently Amended) The component as recited in of one of claims 4 or 5,
wherein the wiring comprises in which metal structures are provided in the wiring levels
(VE), which implement comprising at least one of conductors conductor tracks and
concrete passive components, selected from among the passive components comprising at
least one of capacitors, inductors, and ohmic resistors.

7. (Currently Amended) The component as recited in of claim 1 one of claims 1 to
6, in which the material of wherein the cover (AD) is selected from among comprises one
of ceramic, metal, and glass[[,]]; and

~~in which the material of wherein the frame structure comprises one of is selected~~
~~from among benzocyclobutene, polyimide, and benzoxazol.~~

8. (Currently Amended) The component as recited in of claim 1 one of claims 1 to 7, in which wherein the component is at least one of a microelectronic component, a surface wave component, an FBAR resonator, a micro-optic component, a micromechanical component, or and a hybrid component of the stated types is implemented.

9. (Currently Amended) The component as recited in of claim 2 one of claims 1 to 8, in which wherein the cavity surrounding the component structures (BS) is filled with contains a protective gas having a higher or lower spark-over resistance that is different from a spark-over resistance of than air.

10. (Currently Amended) The component as recited in of claim 1 one of claims 1 to 9, in which all the interfacial connections (DK) are configured to be wherein the connection is conical in shape.

11. (Currently Amended) A method of producing for the production of a hermetically encapsulated components component as recited in one of the preceding claims, comprising:

[[-]] adding component structures (BS) for a plurality of individual components are produced on the front to a first face of a wafer; (W);

[[-]] applying a frame structure (RS) is applied to the first face of the wafer, the frame structure surrounding the component structures; which structure surrounds the

~~component structures (BS) that are assigned to an individual component, in each instance, in ring shape,~~

~~[[-]] the frame structure is glued to a diffusion-proof adhering a cover to the frame structure thereby forming a cavity between the cover and the wafer (AD), so that the component structures assigned to an individual component are disposed in a sealed being inside the cavity, in each instance, [[-]] interfacial connections (DK) are provided in the cover, which connect wherein the cover comprises a first cover face and a second cover face, the second cover face being nearer to the wafer than the first cover face, the first cover face comprising a contact, and wherein the cover comprises a connection that electrically connects the component structures to the contact, on the wafer with contacts (UK) on the underside of the cover, which faces away from the wafer, in electrically conductive manner, [[-]] the interfacial connections are the connection being sealed with a diffusion-proof underside metallization; , from the underside of the cover,~~

~~[[-]] forming a trench pattern of cuts (ES) is produced from the back in a second face of the wafer that does not include the component structures, which the cuts passing through the outer edge region of each frame structure and reaches into the cover, [[-]] wherein the entire back second face of the wafer, including the surfaces exposed in the cuts (ES), is provided with a back face comprises metallization[[,]]; and~~

~~[[-]] a separation of the individual components separating the wafer into individual components along the cuts is carried out.~~

12. (Currently Amended) The method as recited in of claim 11, further comprising:

in which applying an intermediate layer, the intermediate layer being (ZS) is produced together with or in addition to between the frame structure and the cover; and (RS);

in which another adding wiring level (VE) is produced on to the intermediate layer, and the wiring being connected to a with the connector metallization metallizations (AM) on the wafer via the connection (W) by way of interfacial connections (DK).

13. (Currently Amended) The method of claim 12 as recited in claim 11 or 12, in which wherein the intermediate layer comprises a cover film that is glued over to the frame structure (RS) as an intermediate layer (ZS), which film encloses the component structures (BS) in cavities.

14. (Currently Amended) The method of claim as recited in one of claims 11 to 13, in which wherein applying the intermediate layer comprises:

applying the cover film is first applied to and an ancillary film, laminated onto to the frame structure;

structuring the cover film; and

(RS) together with the former, and structured, and in which removing the ancillary film is subsequently removed.

15. (Currently Amended) The method as recited in of claim 14, in which wherein
the cover film is applied to the ancillary film as a reaction resin[[,]] in viscous form, and
wherein structuring comprising laminating and curing cured after lamination.

16. (Currently Amended) The method of claim 11 as recited in one of claims 11 to
15, wherein applying the frame structure comprises shaping the frame structure in which
the frame structure (RS) as well as the intermediate layer (ZS), if present, and/or the cover
film are structured after being applied.

17. (Currently Amended) The method as recited in of claim 12 16, in which the
method for structuring wherein the frame structure (RS) and/or the intermediate layer (ZS)
and/or the cover film is selected from among are applied via photo-structuring, structuring
etching using a resist mask, or laser ablation.

18. (Currently Amended) The method of claim 11 as recited in one of claims 11 to
17, in which a base further comprising:

forming the metallization and is first sputtered on to produce the diffusion-proof
underside metallization (UM) and/or the back face metallization (RM) and/or the wiring
level (VE), and subsequently reinforced by sputtering; and

reinforcing the metallization and the diffusion-proof underside metallization via by
wet chemistry or galvanization galvanically.

19. (Currently Amended) The method as recited in of claim 18, wherein in which
the metallization for the back face metallization (RM) and/or the underside metallization
(UM) and/or the wiring level (VE) is applied over the is formed over an entire area of the
second surface of the wafer; and subsequently structured

wherein forming the metallization and/or the diffusion-proof underside
metallization comprises structuring the metallization and/or the diffusion-proof underside
metallization.

20. (Currently Amended) The method as recited in of claim 12 19, further
comprising:

applying a protective coating to in which the exposed component structures (BS)
are covered with a protective varnish before the whole area metallization for the wiring
level (VE) is added; applied, and

in which removing the protective varnish coating after the wiring is added is
subsequently removed, together with the metallization applied on top of it.

21. (Currently Amended) The method of claim 11 as recited in one of the
preceding claims, further comprising:

roughening a surface of the wafer at a contact point with the frame structure prior
to applying the frame structure in which the surface is roughened, at least in the region of
the frame structure (RS), on the front face of the wafer (W) and/or on the top of the cover
(AD).

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Page : 13

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22. (New) The method of claim 12, wherein applying the intermediate layer comprises shaping the intermediate layer.